

FIG. 1

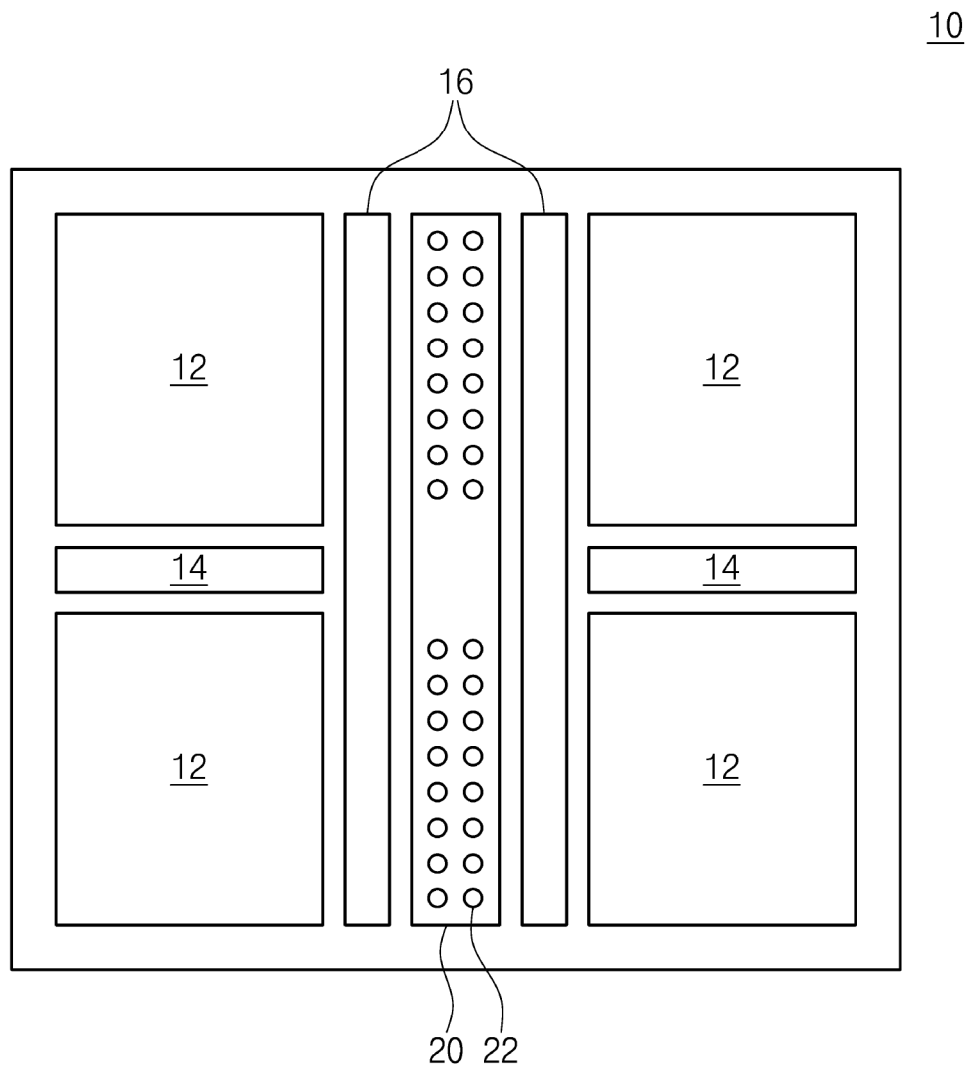


FIG. 2

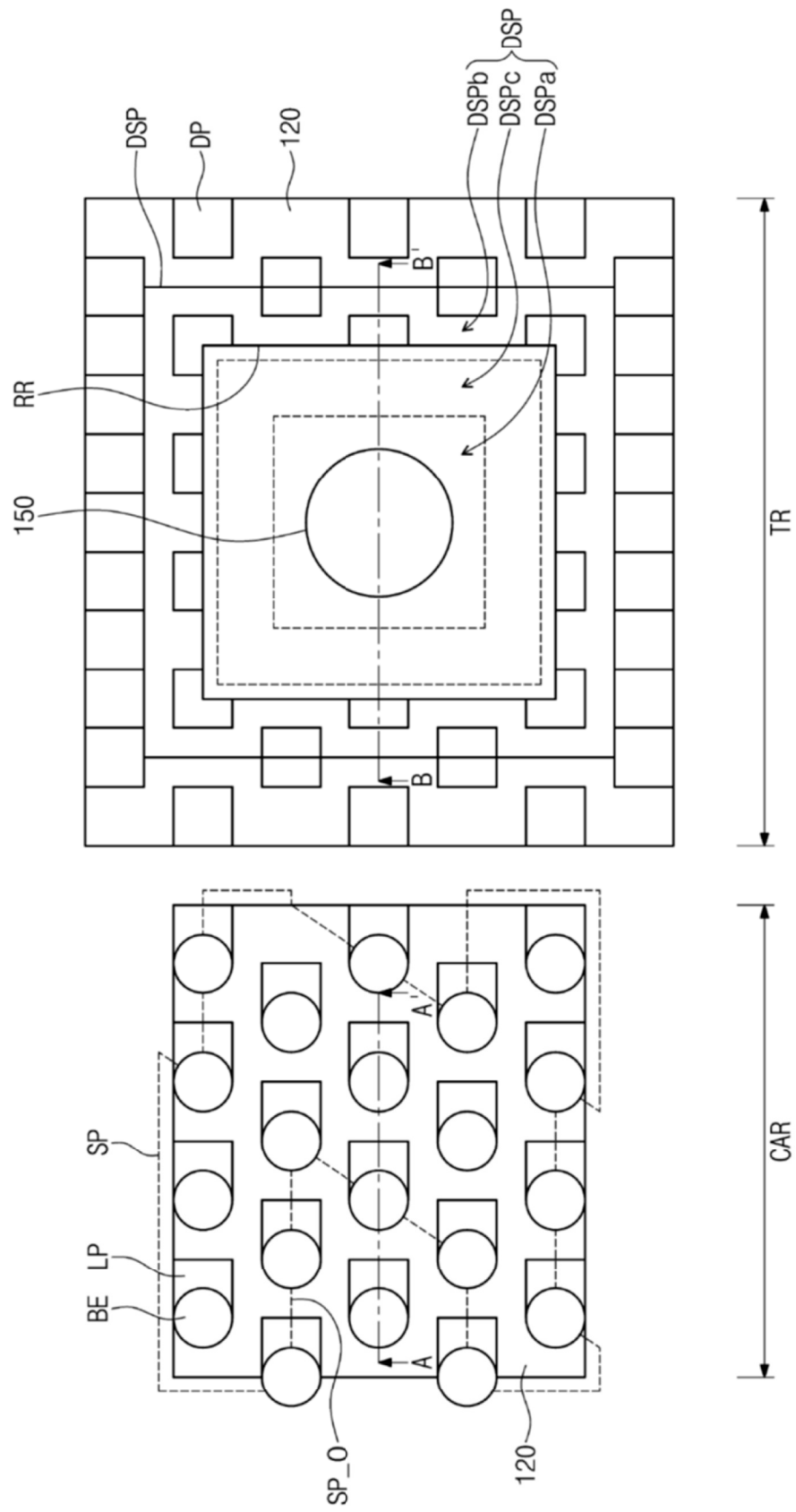


Figure 1 consists of two cross-sectional views, (A) and (B), of a semiconductor device. View (A) shows a top-down perspective with a central region (A') and a surrounding region (A). The central region (A') contains a stack of layers labeled TE, DL, and BE, which are collectively labeled CA. The surrounding region (A) contains a stack of layers labeled TE, DL, BE, and CA, which are collectively labeled CA. The layers are numbered 100, 110, 120, 130, 140, 142, 144, and 146. View (B) shows a side perspective with a central region (B') and a surrounding region (B). The central region (B') contains a stack of layers labeled TE, DL, and BE, which are collectively labeled CA. The surrounding region (B) contains a stack of layers labeled TE, DL, BE, and CA, which are collectively labeled CA. The layers are numbered 100, 110, 120, 130, 140, 142, 144, and 146. The device includes a central region (A') and a surrounding region (A) with various layers and structures.

[illegible]

FIG. 5

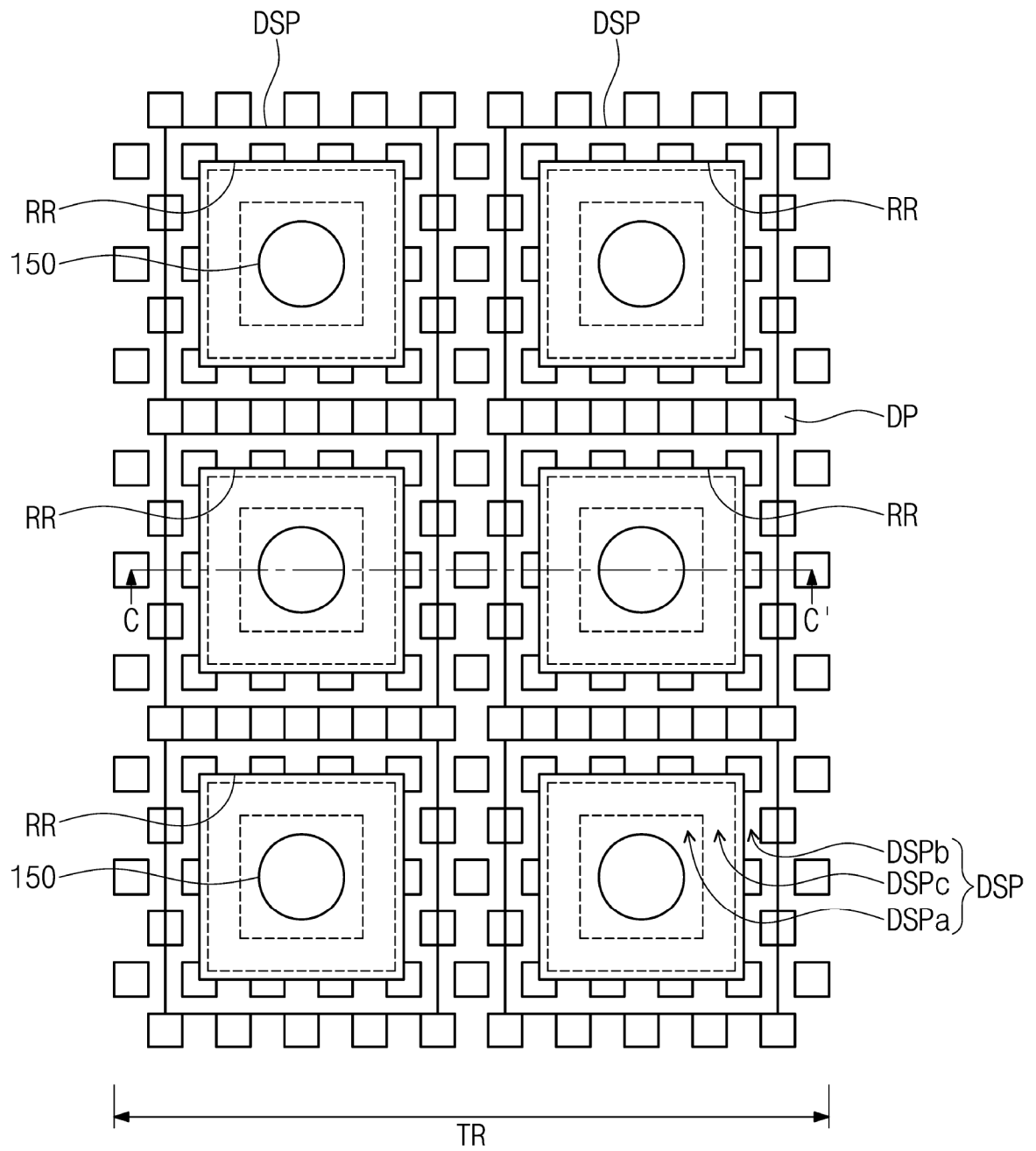


FIG. 6

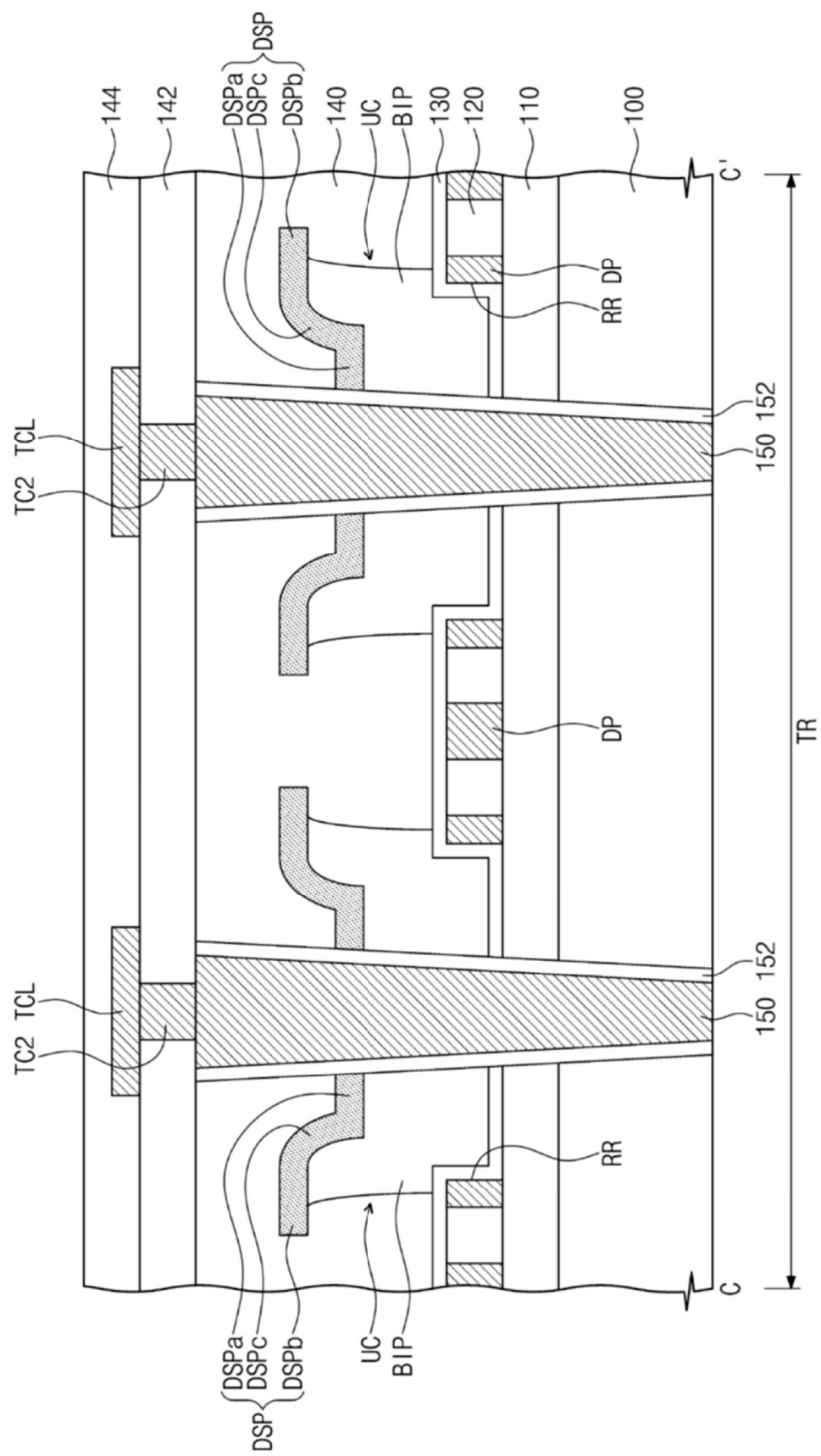


FIG. 7

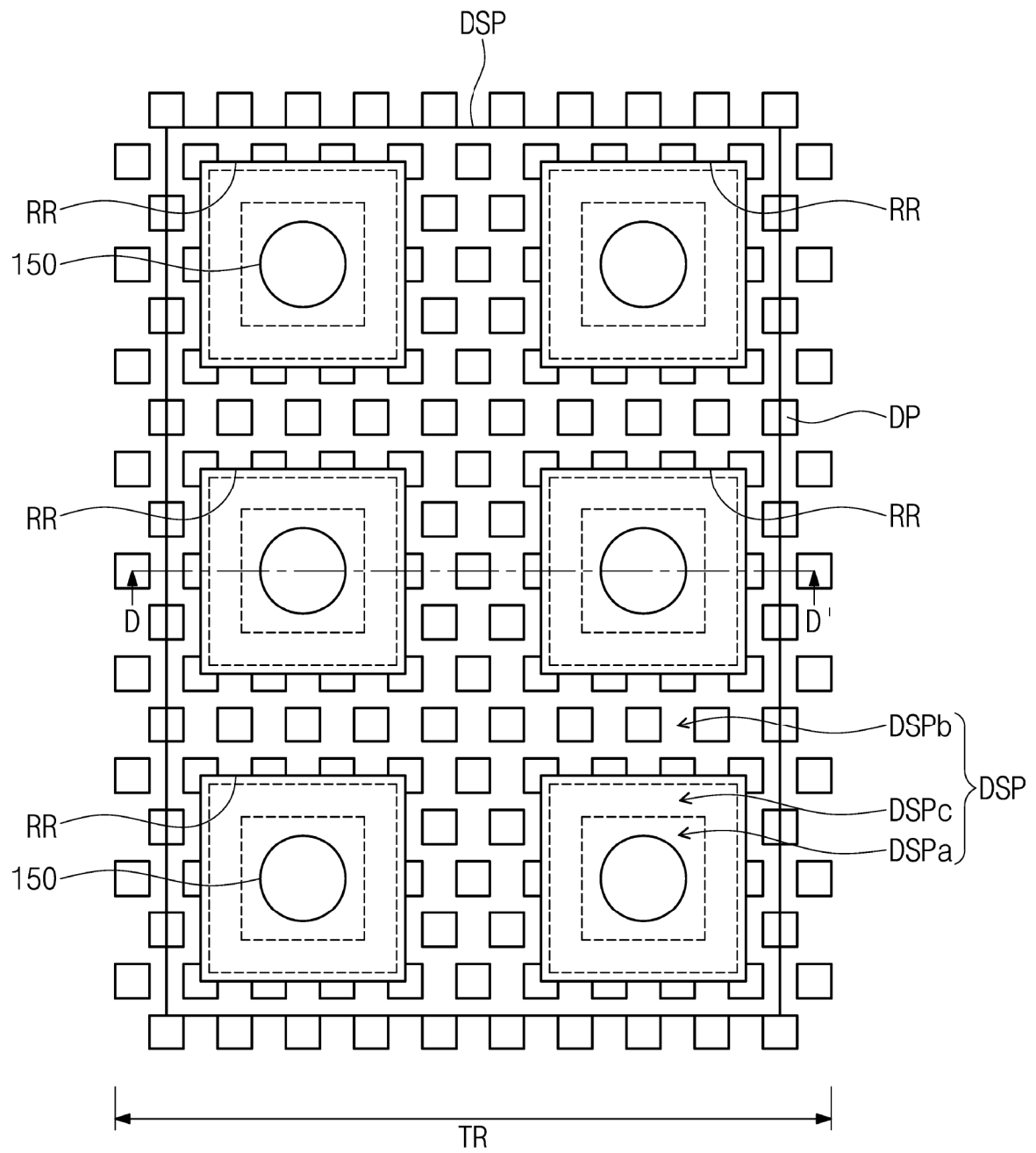


FIG. 8

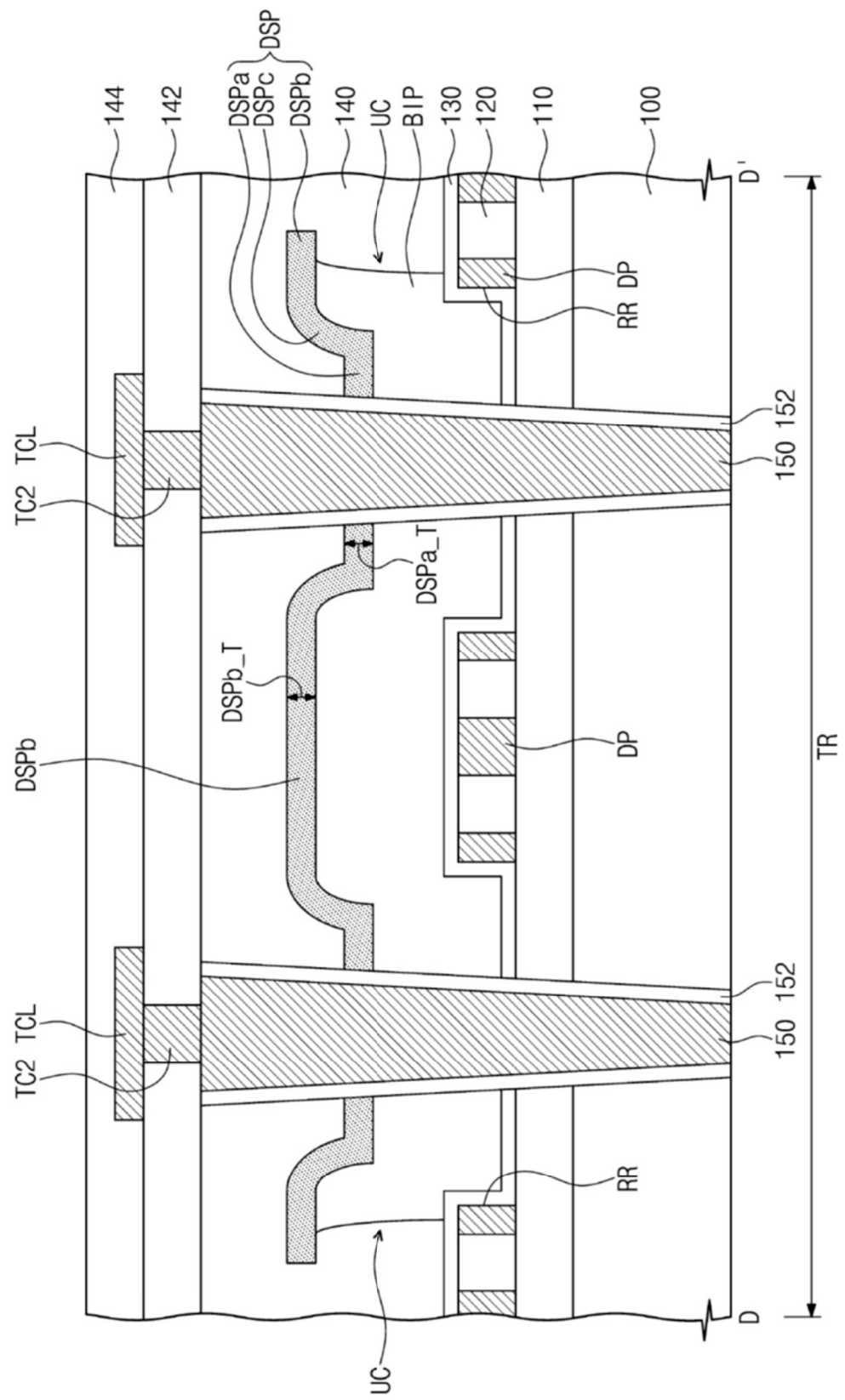


FIG. 9A

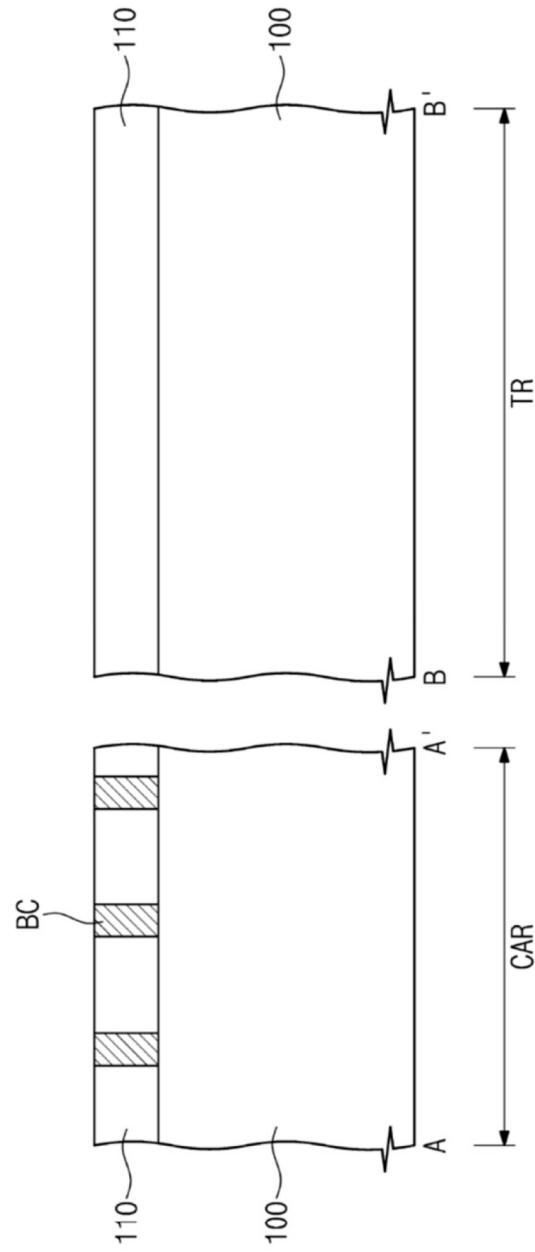


FIG. 9B

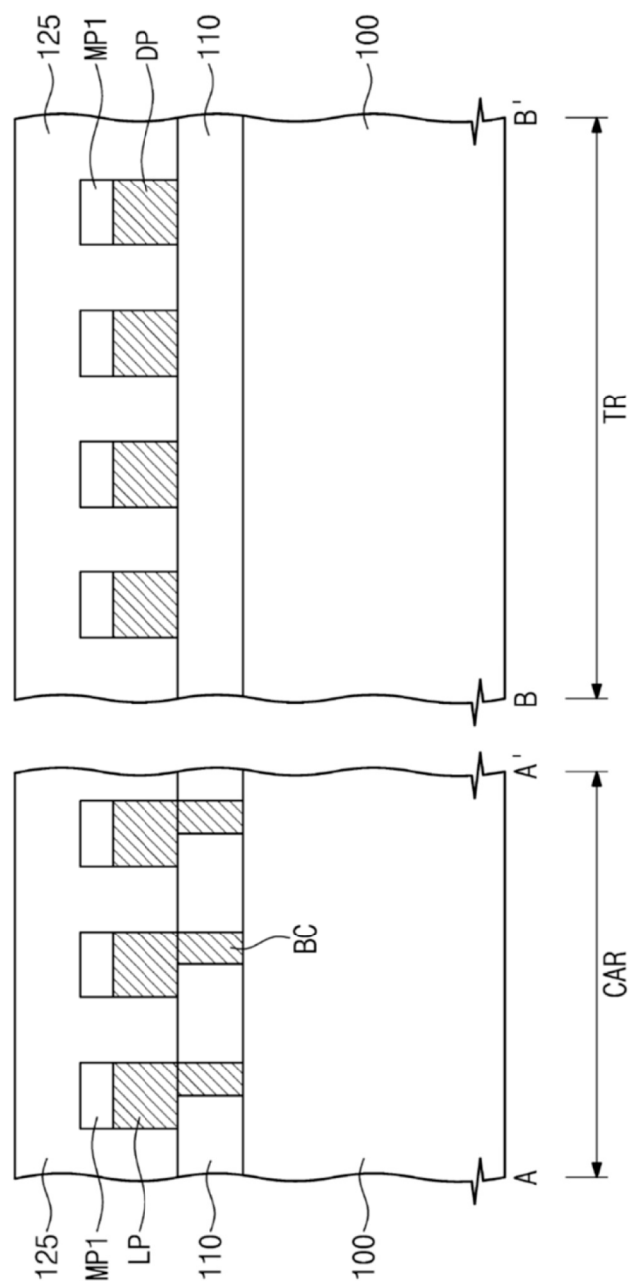


FIG. 9C

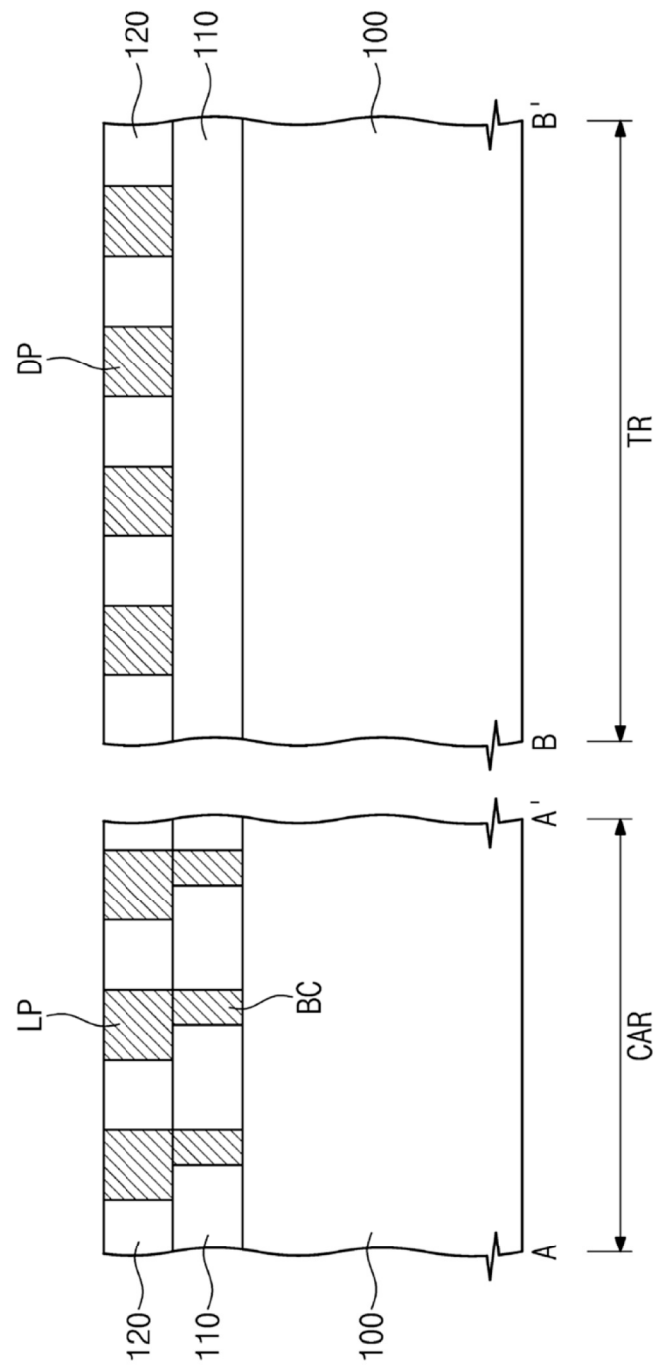


FIG. 9D

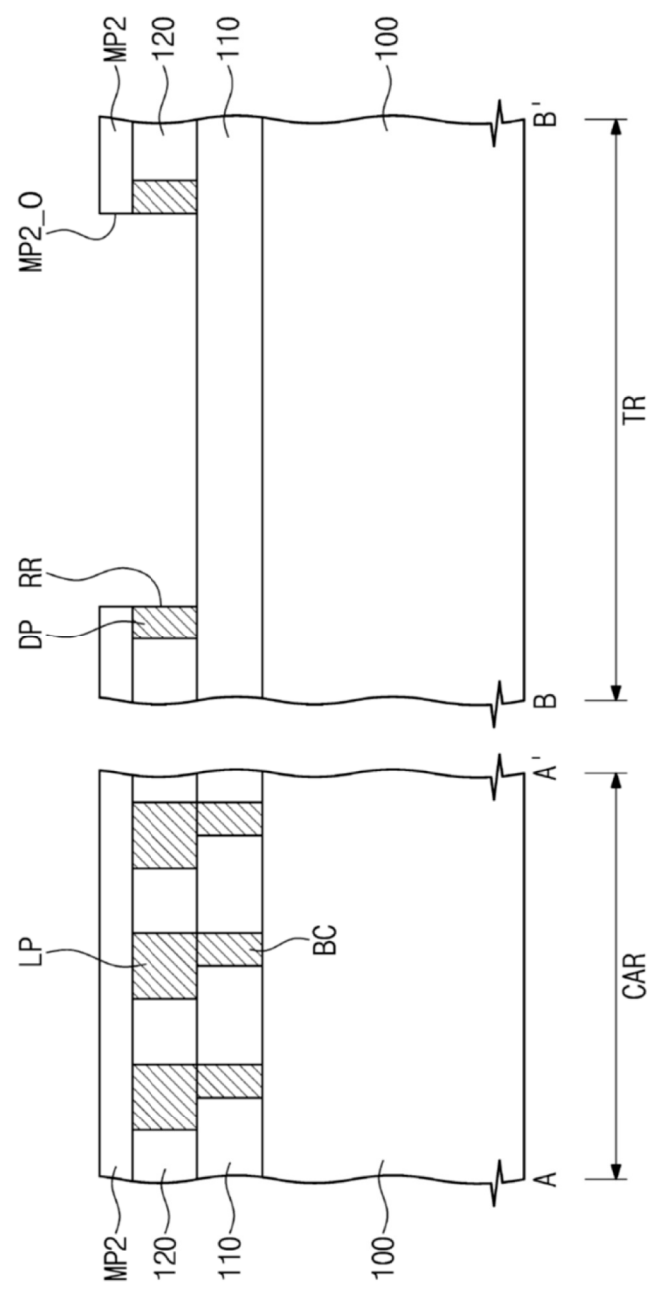


FIG. 9E

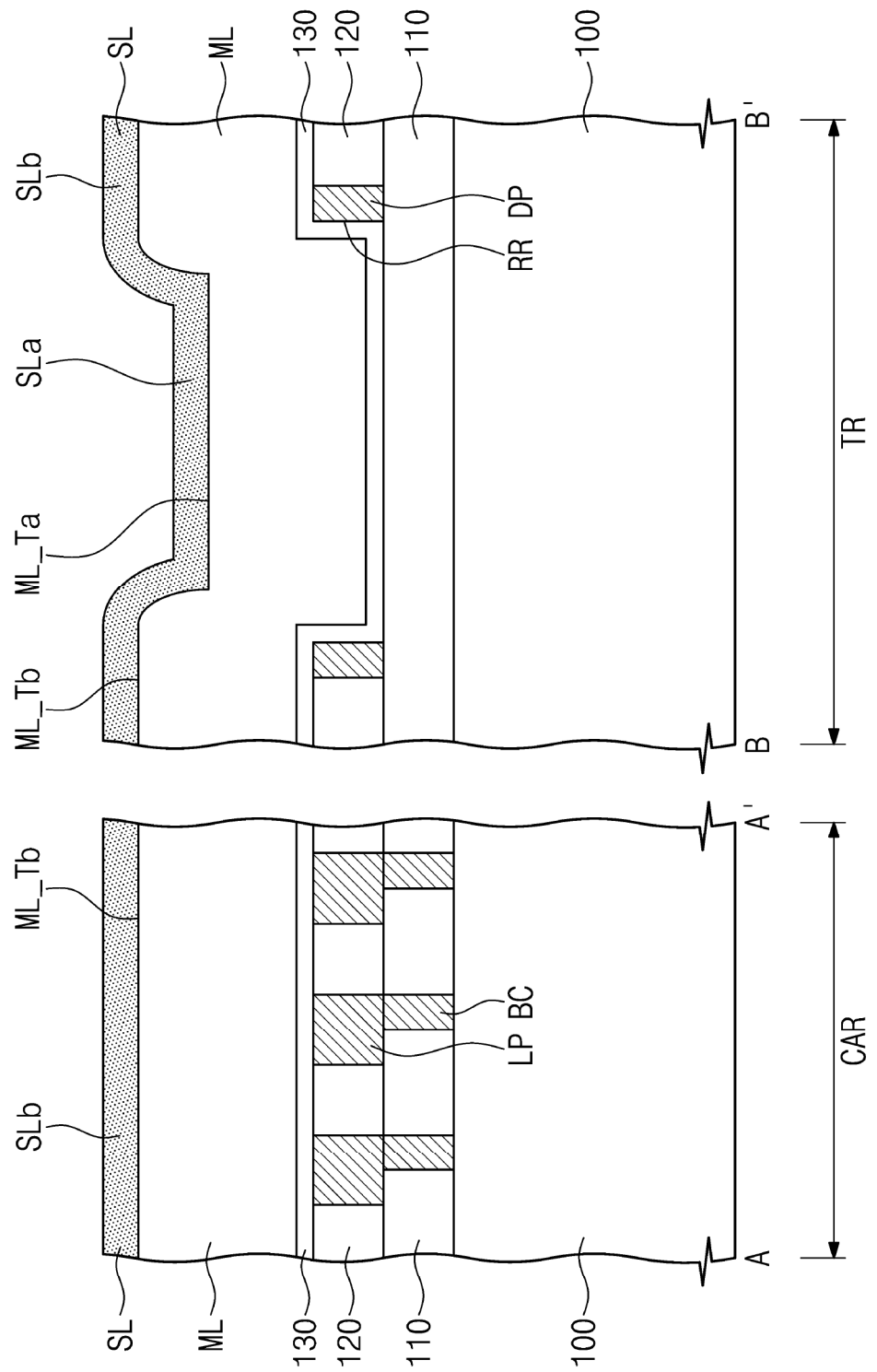


FIG. 9F

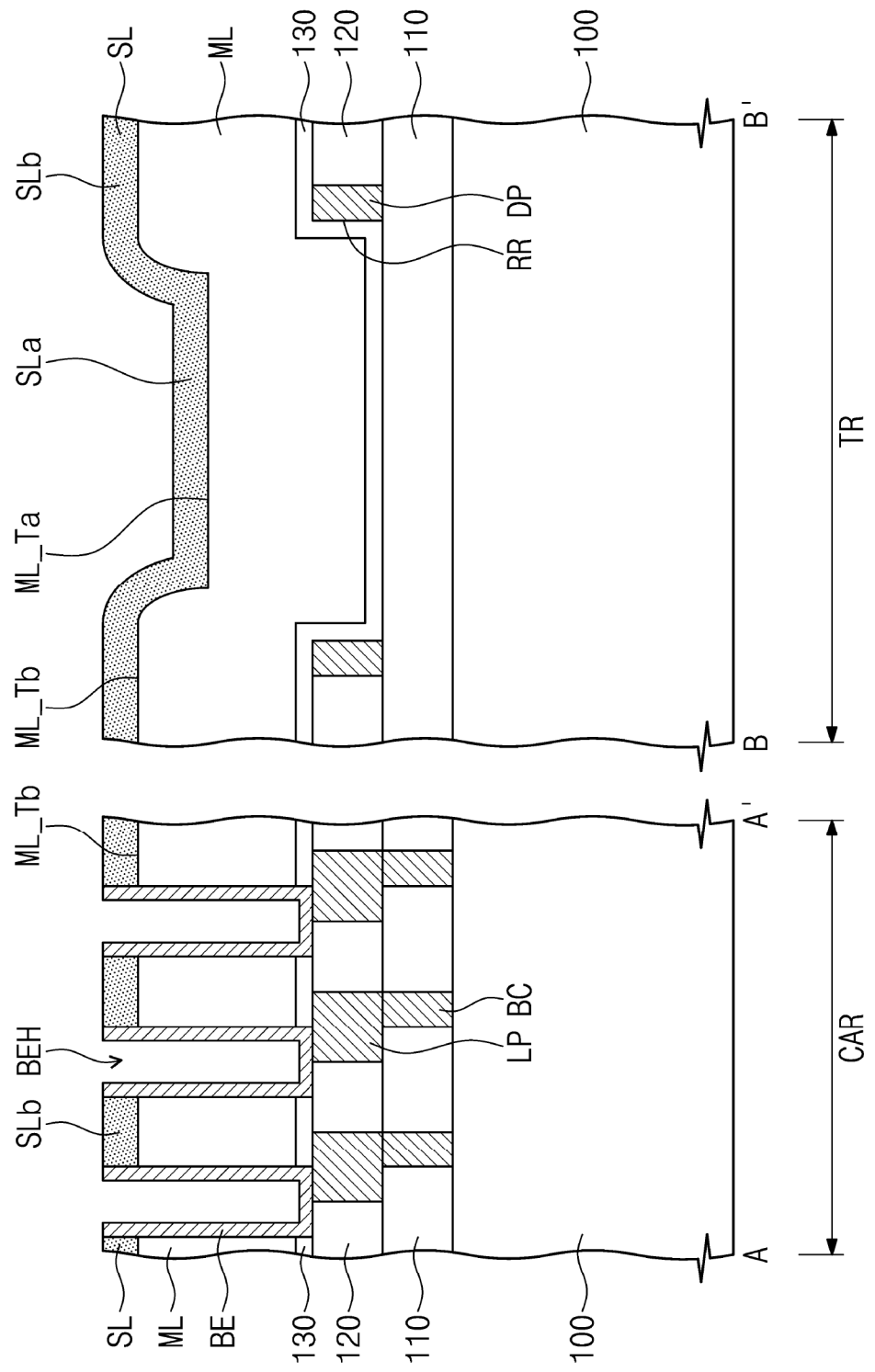


FIG. 9G

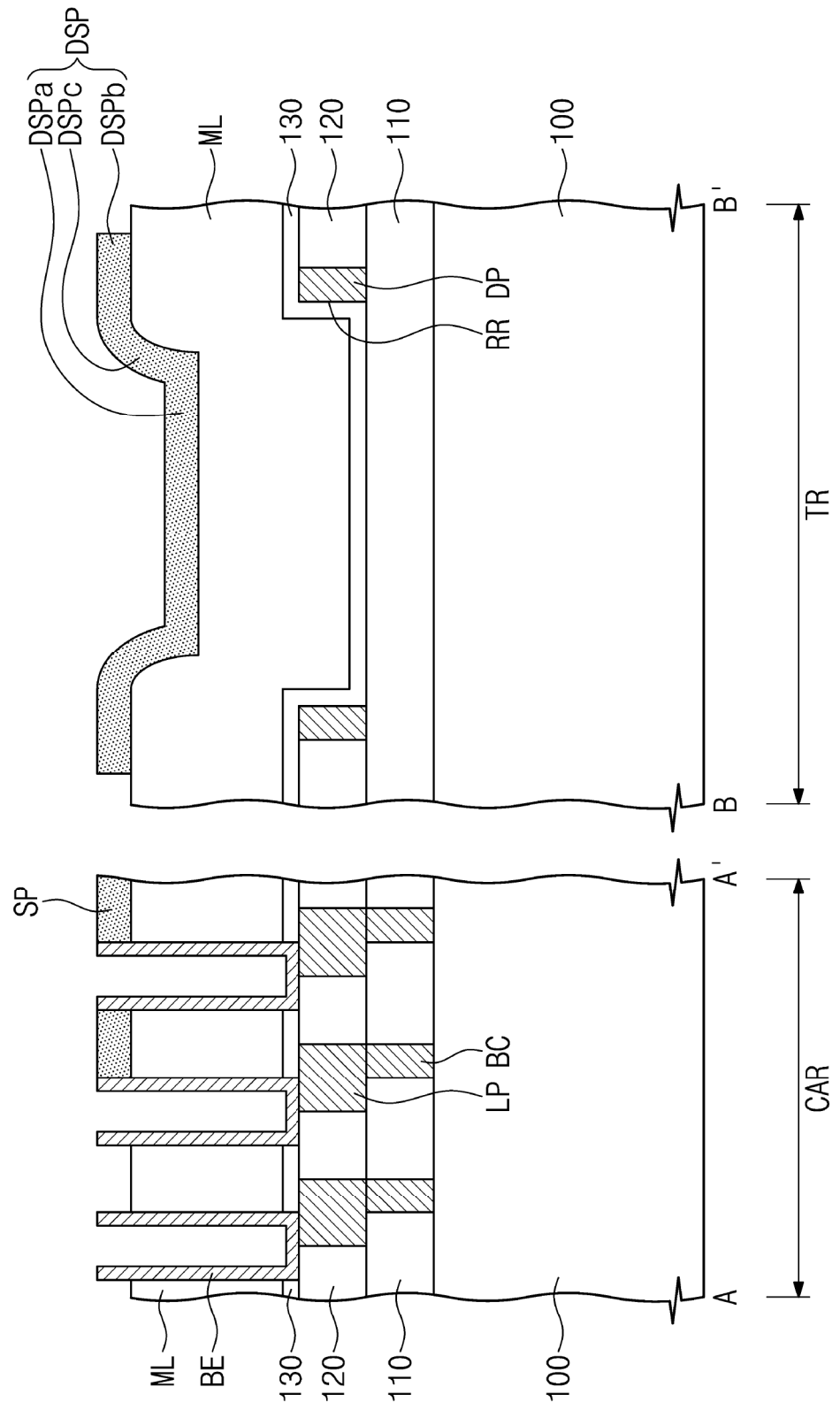


FIG. 9H

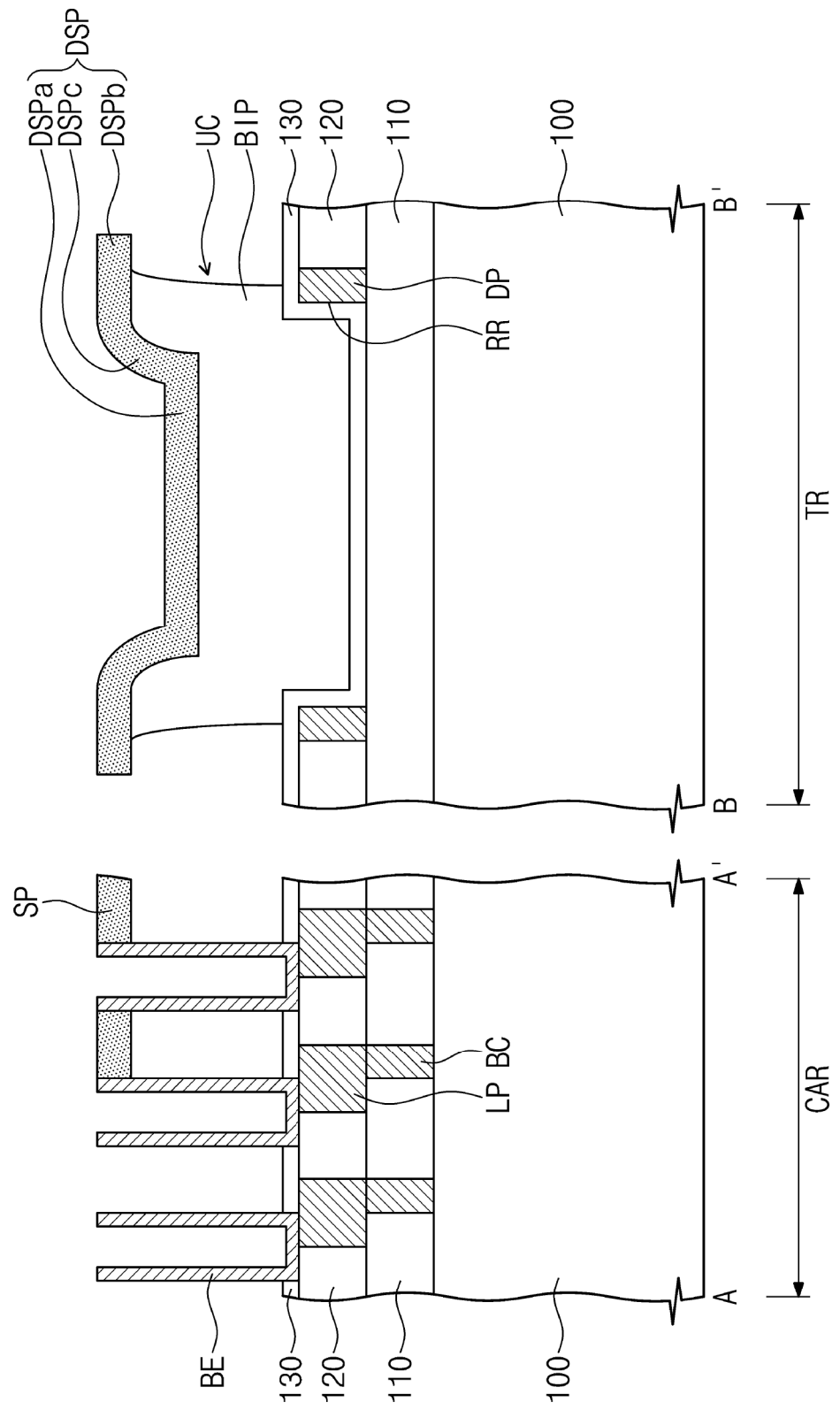


FIG. 9I

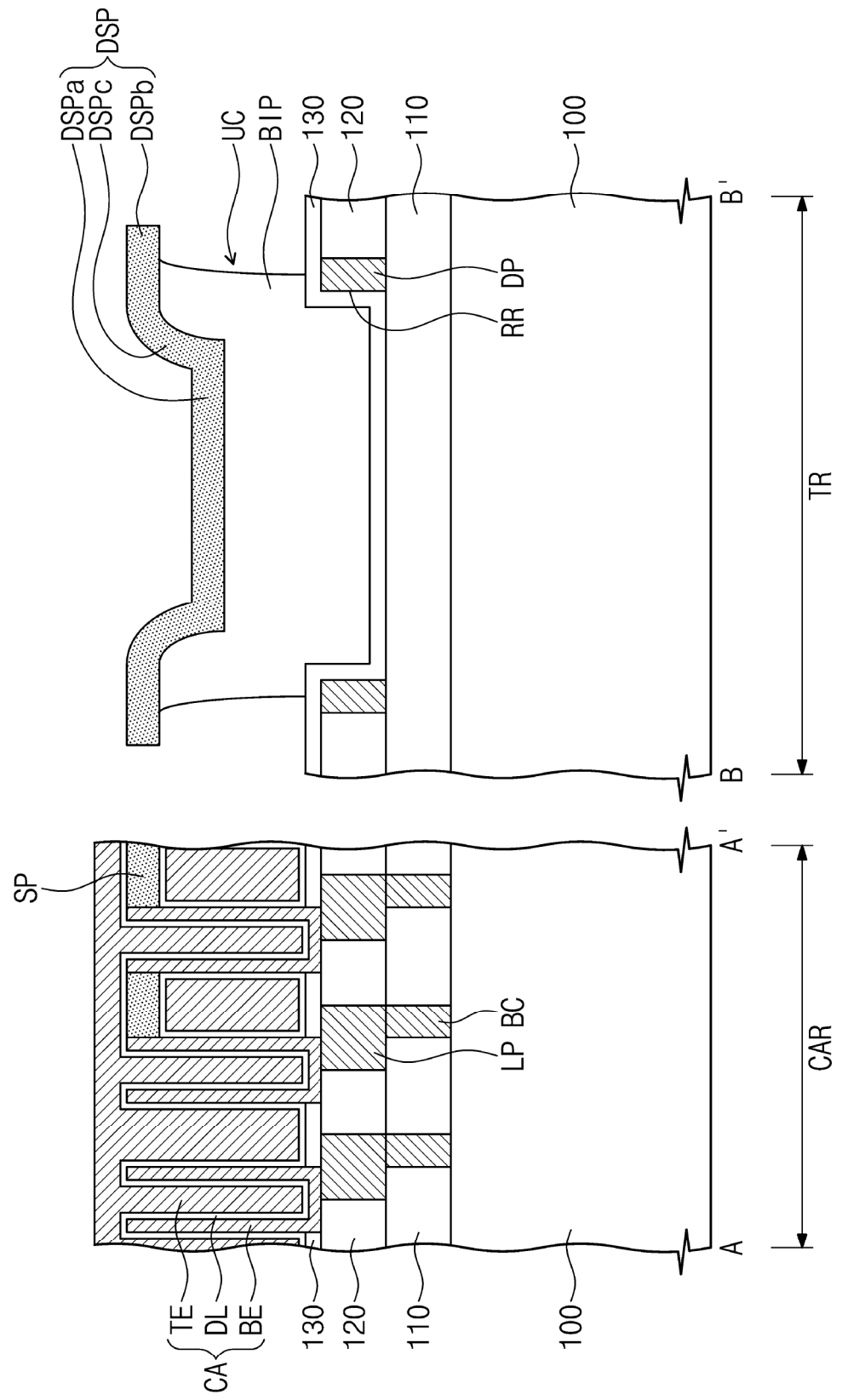


FIG. 9J

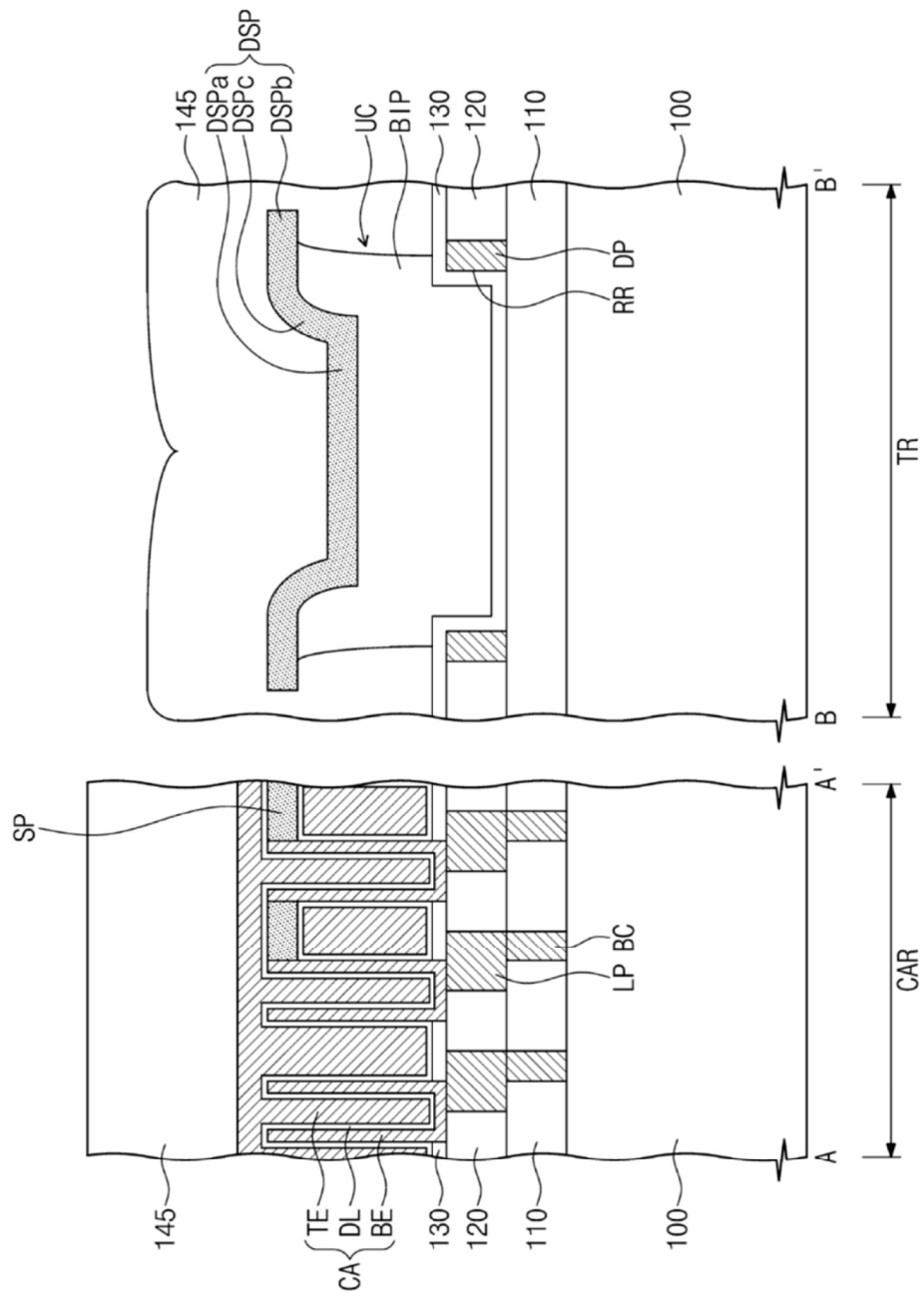


FIG. 9K

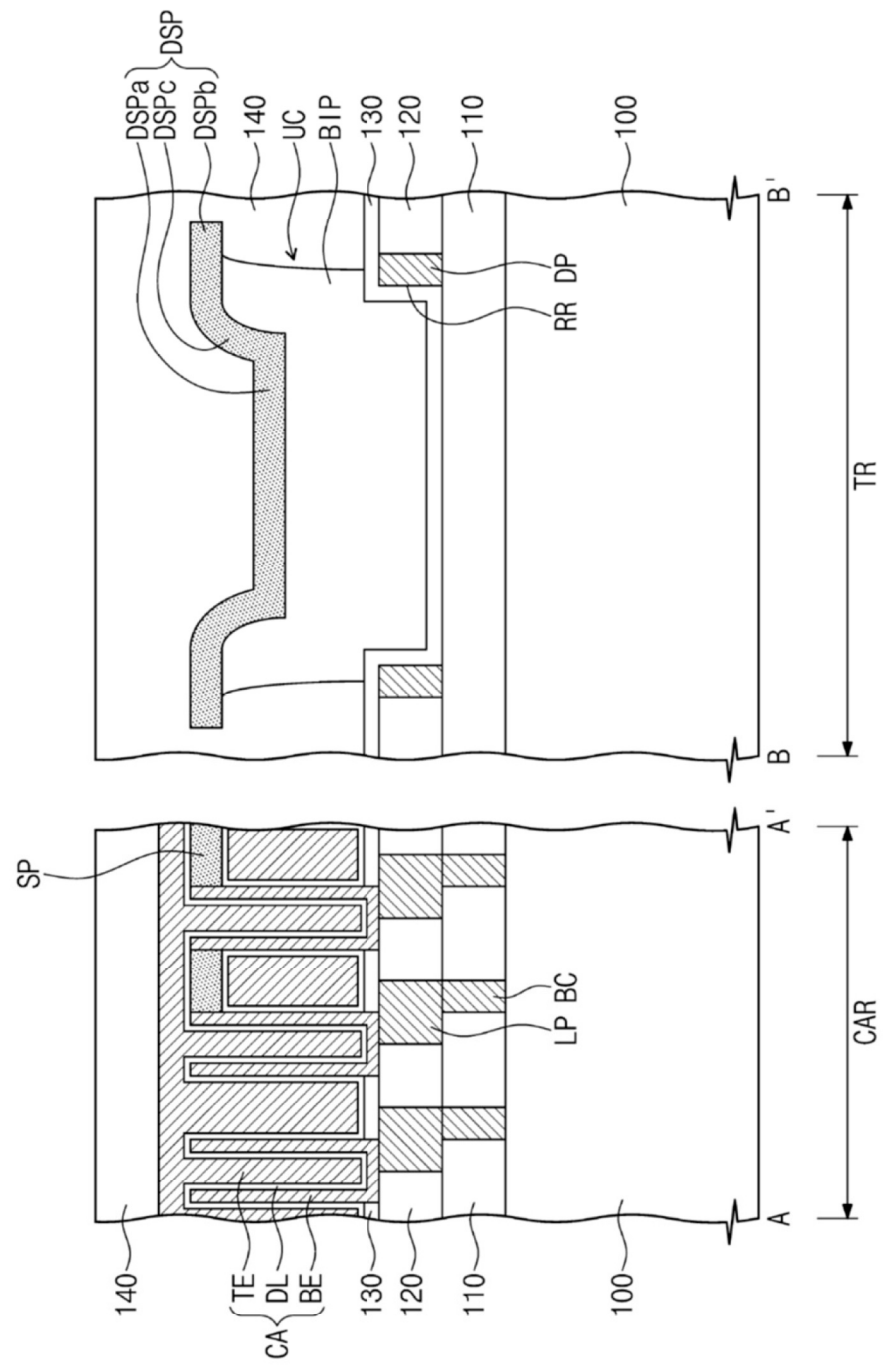


FIG. 9L

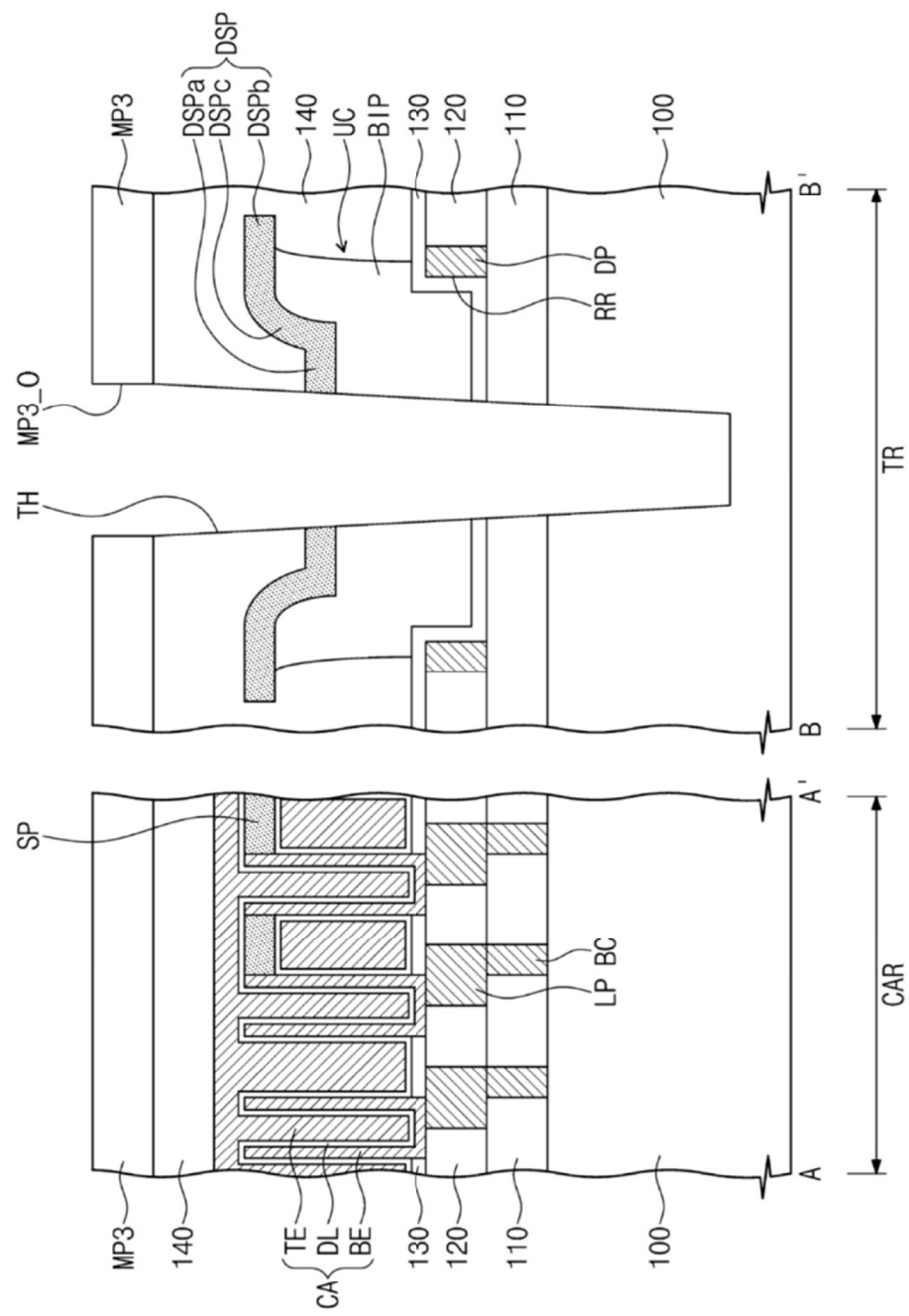


FIG. 9M

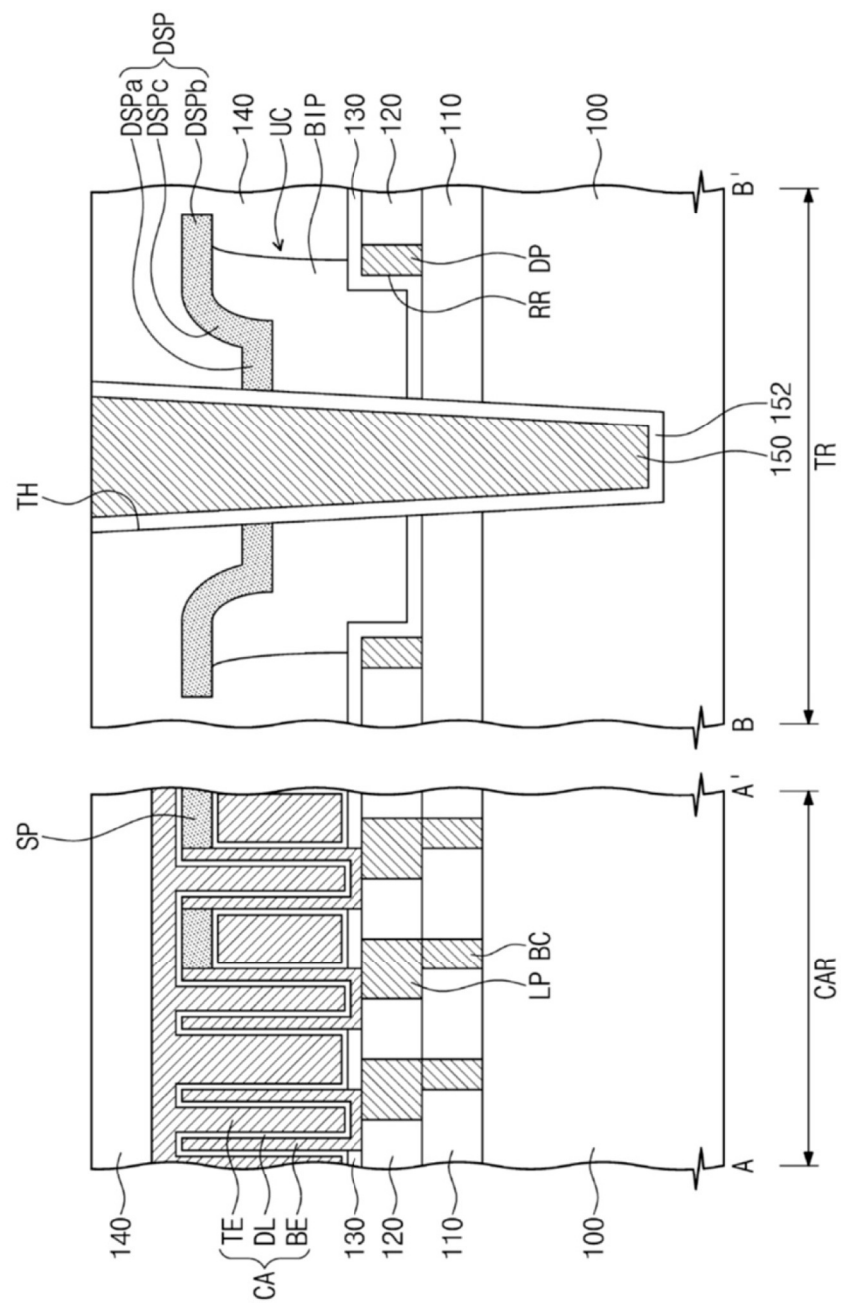


FIG. 9N

